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J23-883

U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU
10092795	03/06/2002	438		2813

EXAMINER  
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I. PHAM

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\*\*CONTINUING DATA VERIFIED: *TN*  
*None*

\*\* FOREIGN APPLICATIONS VERIFIED: *None*  
*TN*

PG-PUB DO NOT PUBLISH ☐

RESCIND ☐

Foreign priority claimed ☐ yes ☒ no  
35 USC 119 conditions met ☐ yes ☒ no  
Verified and Acknowledged Examiners's initials *TN*

ATTORNEY DOCKET NO

7017/ETCH/CORE

TITLE : Method of plasma etching of high-K dielectric materials with high selectivity to underlying layers  
U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED

Assistant Examiner

CLAIMS ALLOWED

Total Claims ☐ Partial Claim for 0.0

ISSUE FEE

Amount Due ☐ Date Paid ☐

DRAWING

Sheet 1 of 1 ☐ Figures ☐ Photo ☐

Primary Examiner

PREPARED FOR ISSUE

Application Examiner

☐ TERMINAL  
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